



# BUK9E06-55A

N-channel TrenchMOS logic level FET

Rev. 04 — 31 May 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V and 24 V loads
- Motors, lamps and solenoids
- Automotive and general purpose power switching

### 1.4 Quick reference data

Table 1. Quick reference data

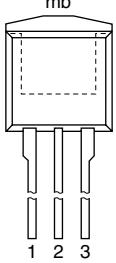
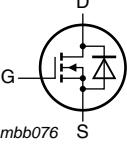
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25^\circ\text{C}; T_j \leq 175^\circ\text{C}$	-	-	55	V
$I_D$	drain current	$V_{GS} = 5\text{ V}; T_j = 25^\circ\text{C}$ ; see <a href="#">Figure 3</a> ; see <a href="#">Figure 1</a>	[1]	-	75	A
$P_{tot}$	total power dissipation	$T_{mb} = 25^\circ\text{C}$ ; see <a href="#">Figure 2</a>	-	-	300	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25^\circ\text{C}$	-	4.8	5.8	$\text{m}\Omega$
		$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 25^\circ\text{C}$	-	-	6.7	$\text{m}\Omega$
		$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 25^\circ\text{C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	5.3	6.3	$\text{m}\Omega$
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}; V_{sup} \leq 55\text{ V}; R_{GS} = 50\text{ }\Omega; V_{GS} = 5\text{ V}; T_{j(init)} = 25^\circ\text{C}$ ; unclamped	-	-	1.1	J

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[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain	 <b>SOT226 (I2PAK)</b>	

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BUK9E06-55A	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

## 4. Limiting values

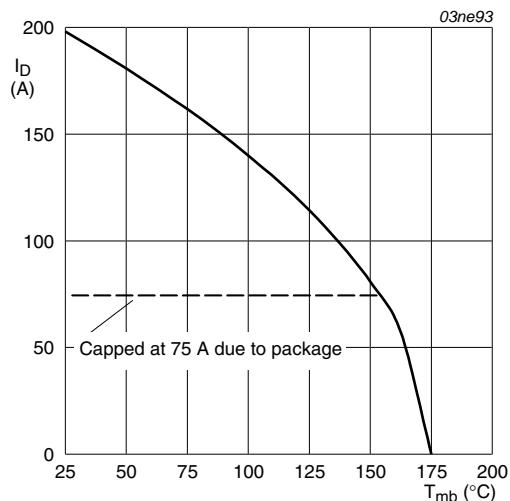
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25^\circ\text{C}; T_j \leq 175^\circ\text{C}$	-	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	-	55	V
$V_{GS}$	gate-source voltage		-15	-	15	V
$I_D$	drain current	$V_{GS} = 5\text{ V}; T_j = 25^\circ\text{C};$ see <a href="#">Figure 3</a> ; see <a href="#">Figure 1</a>	[1]	-	-	154 A
		$V_{GS} = 5\text{ V}; T_j = 100^\circ\text{C};$ see <a href="#">Figure 1</a>	[2]	-	-	75 A
$I_{DM}$	peak drain current	$T_{mb} = 25^\circ\text{C}; t_p \leq 10\text{ }\mu\text{s};$ pulsed; see <a href="#">Figure 3</a>	-	-	616	A
$P_{tot}$	total power dissipation	$T_{mb} = 25^\circ\text{C};$ see <a href="#">Figure 2</a>	-	-	300	W
$T_{stg}$	storage temperature		-55	-	175	°C
$T_j$	junction temperature		-55	-	175	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25^\circ\text{C}$	[1]	-	-	154 A
			[2]	-	-	75 A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s};$ pulsed; $T_{mb} = 25^\circ\text{C}$	-	-	616	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}; V_{sup} \leq 55\text{ V}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 5\text{ V}; T_{j(init)} = 25^\circ\text{C};$ unclamped	-	-	1.1	J

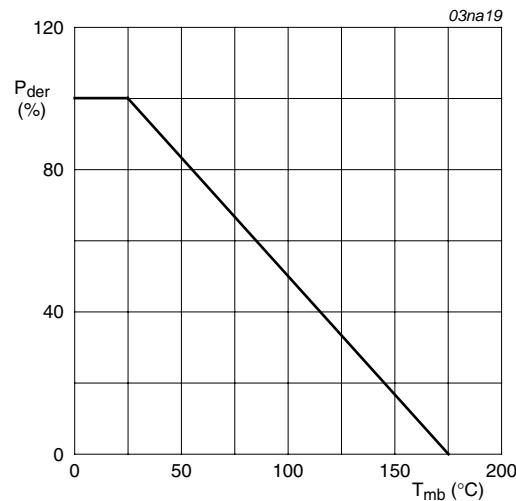
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.



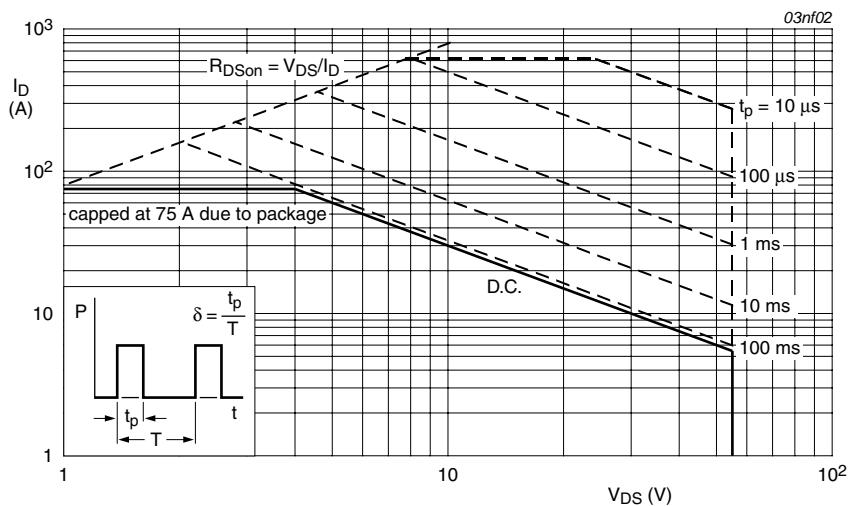
$$V_{GS} \geq 5V$$

**Fig 1. Normalized continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot}(25^\circ\text{C})} \times 100 \%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



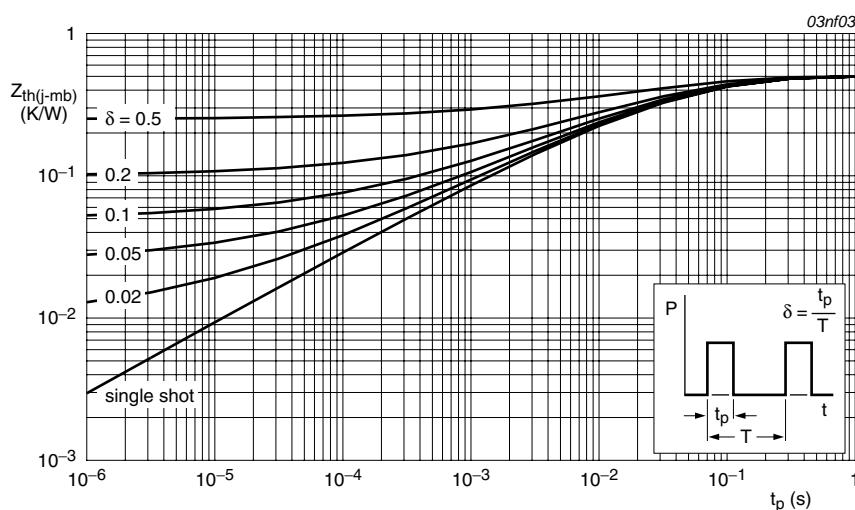
$$T_{mb} = 25^\circ\text{C}; I_{DM} \text{ is single pulse}$$

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.5	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

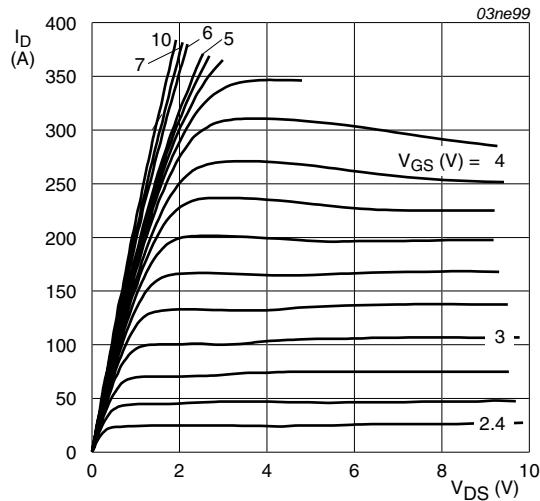
## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	55	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA

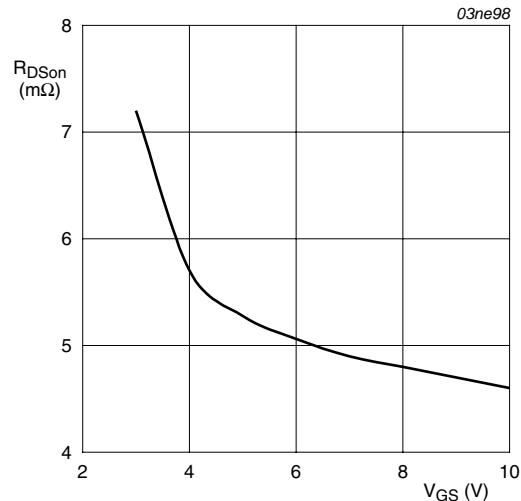
**Table 6. Characteristics ...continued**

<b>Symbol</b>	<b>Parameter</b>	<b>Conditions</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	-	13.2	$\text{m}\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	4.8	5.8	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	-	6.7	$\text{m}\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	5.3	6.3	$\text{m}\Omega$
<b>Dynamic characteristics</b>						
$C_{iss}$	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}$	-	6500	8600	$\text{pF}$
$C_{oss}$	output capacitance	$T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 14</a>	-	1000	1200	$\text{pF}$
$C_{rss}$	reverse transfer capacitance		-	650	850	$\text{pF}$
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V}$	-	45	-	$\text{ns}$
$t_r$	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	180	-	$\text{ns}$
$t_{d(off)}$	turn-off delay time		-	420	-	$\text{ns}$
$t_f$	fall time		-	235	-	$\text{ns}$
$L_D$	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	$\text{nH}$
		from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	2.5	-	$\text{nH}$
$L_S$	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	$\text{nH}$
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 30 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ ; see <a href="#">Figure 15</a>	-	0.85	1.2	$\text{V}$
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}$	-	80	-	$\text{ns}$
$Q_r$	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	200	-	$\text{nC}$



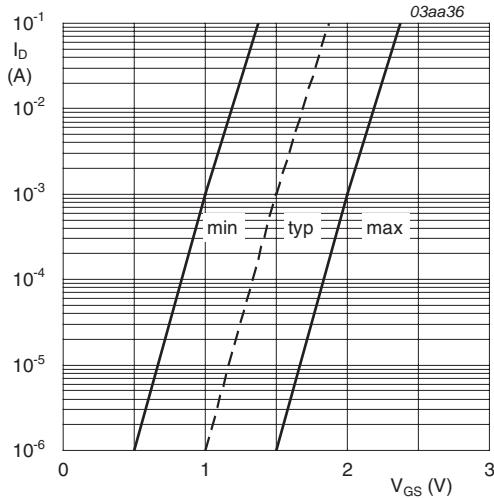
$T_j = 25^\circ C; t_p = 300\mu s$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



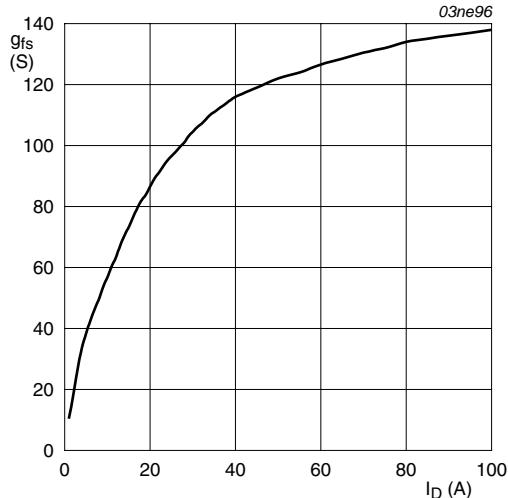
$T_j = 25^\circ C; I_D = 25A$

**Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values**



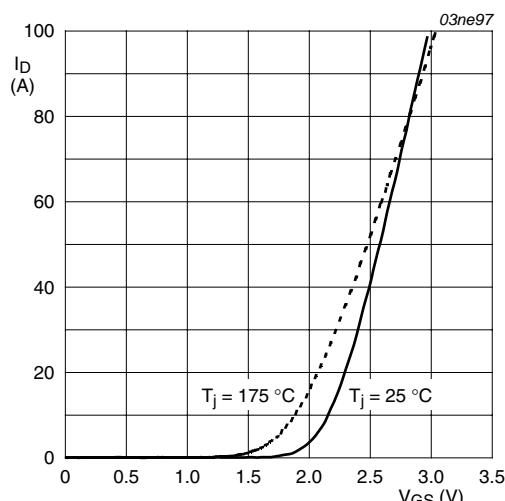
$T_j = 25^\circ C; V_{DS} = V_{GS}$

**Fig 7. Sub-threshold drain current as a function of gate-source voltage**



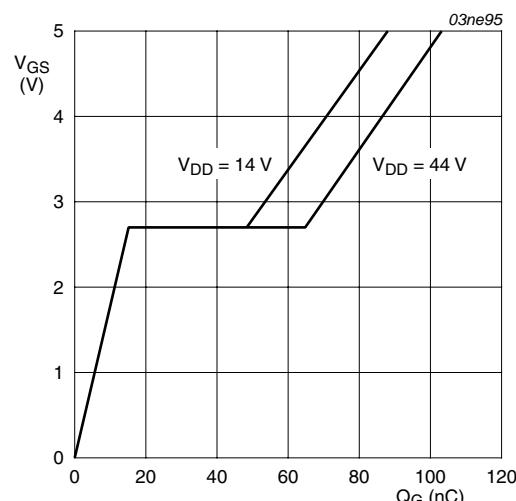
$T_j = 25^\circ C; V_{DS} = 25V$

**Fig 8. Forward transconductance as a function of drain current; typical values**



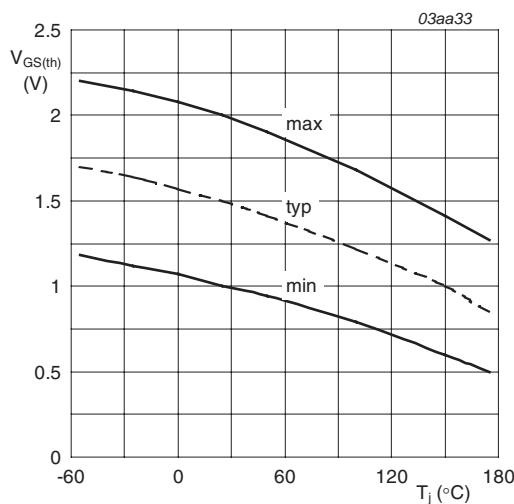
$V_{DS} = 25\text{ V}$

**Fig 9.** Transfer characteristics: drain current as a function of gate-source voltage; typical values



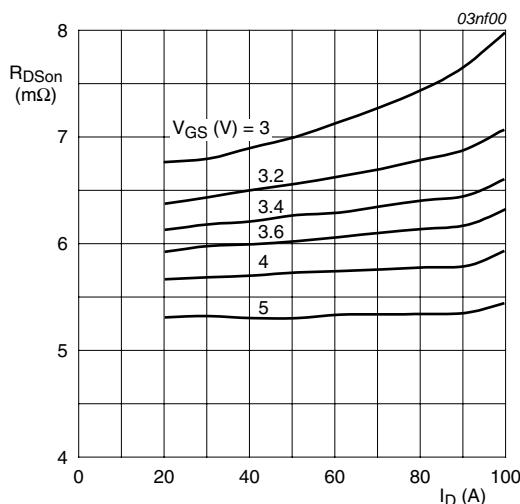
$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

**Fig 10.** Gate-source voltage as a function of gate charge; typical values



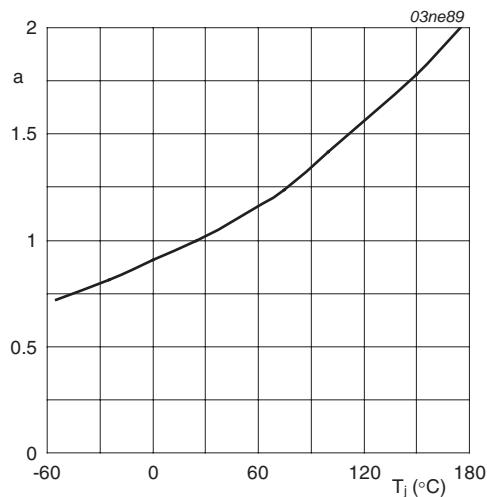
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

**Fig 11.** Gate-source threshold voltage as a function of junction temperature



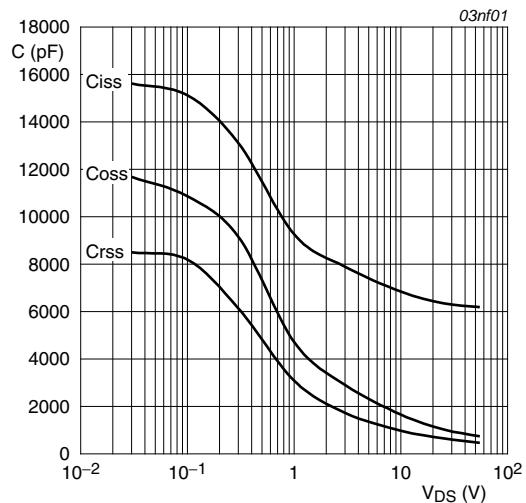
$T_j = 25\text{ }^{\circ}\text{C}$

**Fig 12.** Drain-source on-state resistance as a function of drain current; typical values



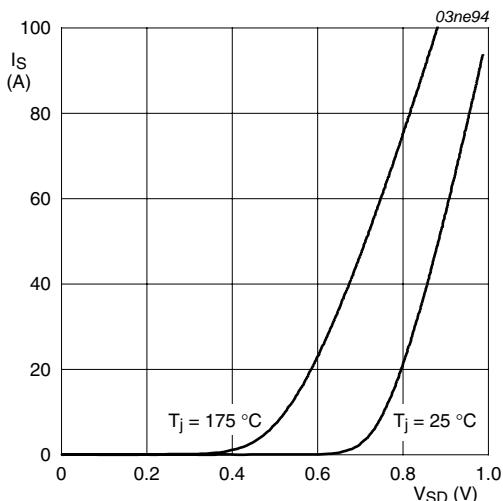
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

**Fig 13.** Normalized drain-source on-state resistance factor as a function of junction temperature



$$V_{GS} = 0V; f = 1MHz$$

**Fig 14.** Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$$V_{GS} = 0V$$

**Fig 15.** Reverse diode current as a function of reverse diode voltage; typical values

## 7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226

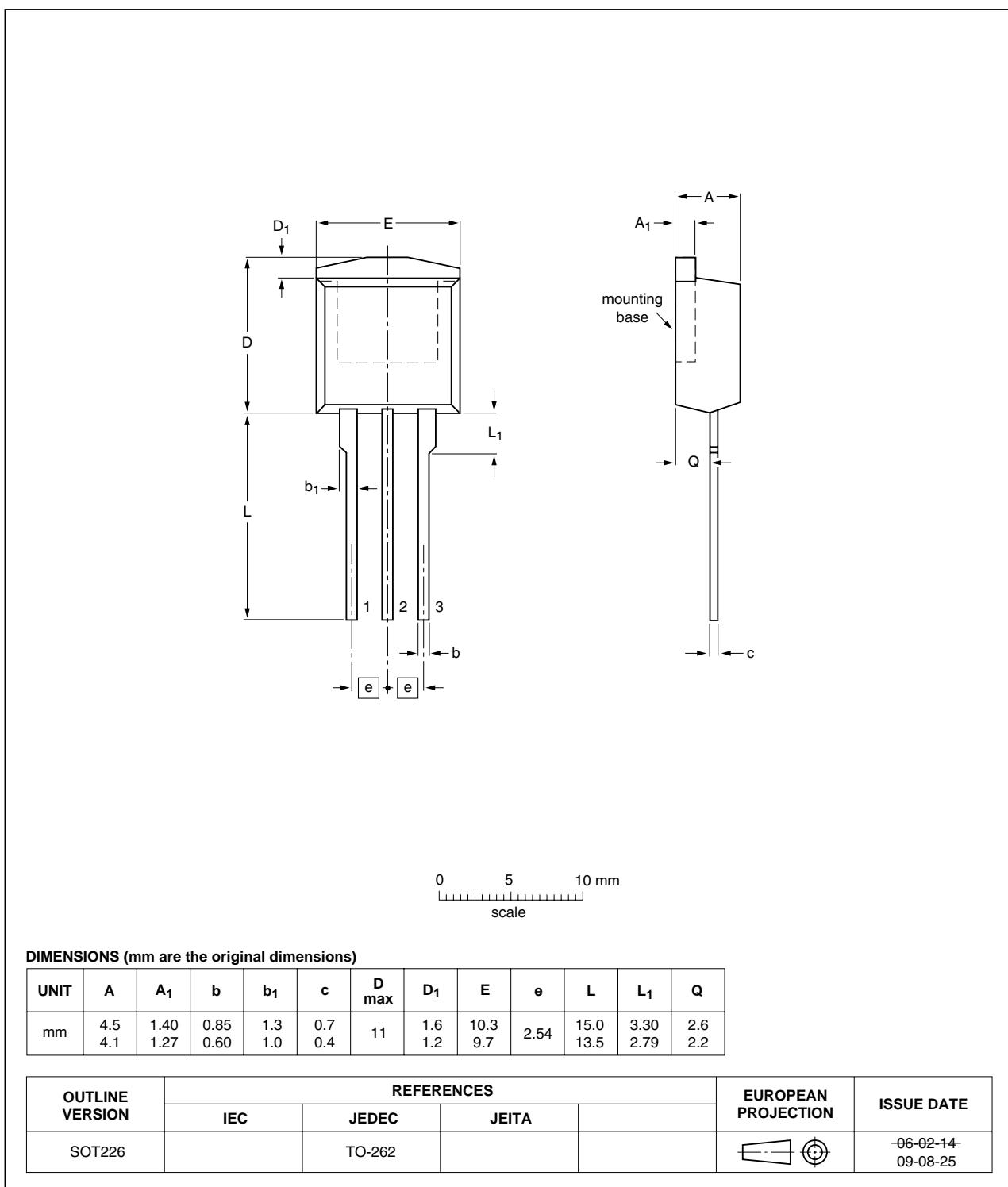


Fig 16. Package outline SOT226 (I2PAK)

## 8. Revision history

**Table 7. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9E06-55A v.4	20100531	Product data sheet	-	BUK9506_9606_9E06_55A-03
Modifications:	<ul style="list-style-type: none"><li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>Legal texts have been adapted to the new company name where appropriate.</li><li>Type number BUK9E06-55A separated from data sheet BUK9506_9606_9E06_55A-03.</li></ul>			
BUK9506_9606_9E06_55A-03 (9397 750 08416)	20010723	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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